

N-Channel 800V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	800	
$R_{DS(on)}$ typ. (Ω) at 25 °C	$V_{GS} = 10$ V	0.550

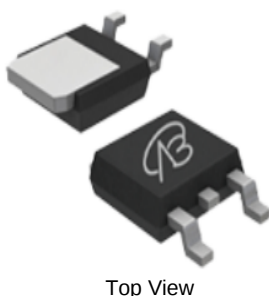
FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)

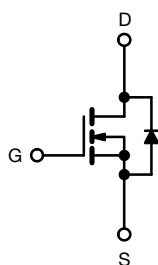


RoHS
COMPLIANT
HALOGEN
FREE

TO-252



Top View



N-Channel MOSFET

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Renewable energy
 - Solar (PV inverters)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V _{DS}	800	V
Gate-source voltage			V _{GS}	± 30	
Continuous drain current (T _J = 150 °C)	V _{GS} at 10 V	T _C = 25 °C	I _D	8	A
		T _C = 100 °C		5	
Pulsed drain current ^a			I _{DM}	24	
Linear derating factor				1.7	W/°C
Single pulse avalanche energy ^b			E _{AS}	330	mJ
Maximum power dissipation			P _D	180	W
Operating junction and storage temperature range			T _J , T _{stg}	-55 to +150	°C
Drain-source voltage slope	T _J = 125 °C		dV/dt	50	V/ns
Reverse diode dV/dt ^d				5.1	
Soldering recommendations (peak temperature) ^c	For 10 s			260	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 100$ V, starting $T_J = 25$ °C, $L = 30$ mH, $R_g = 25$ Ω , $I_{AS} = 4$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	0.85	

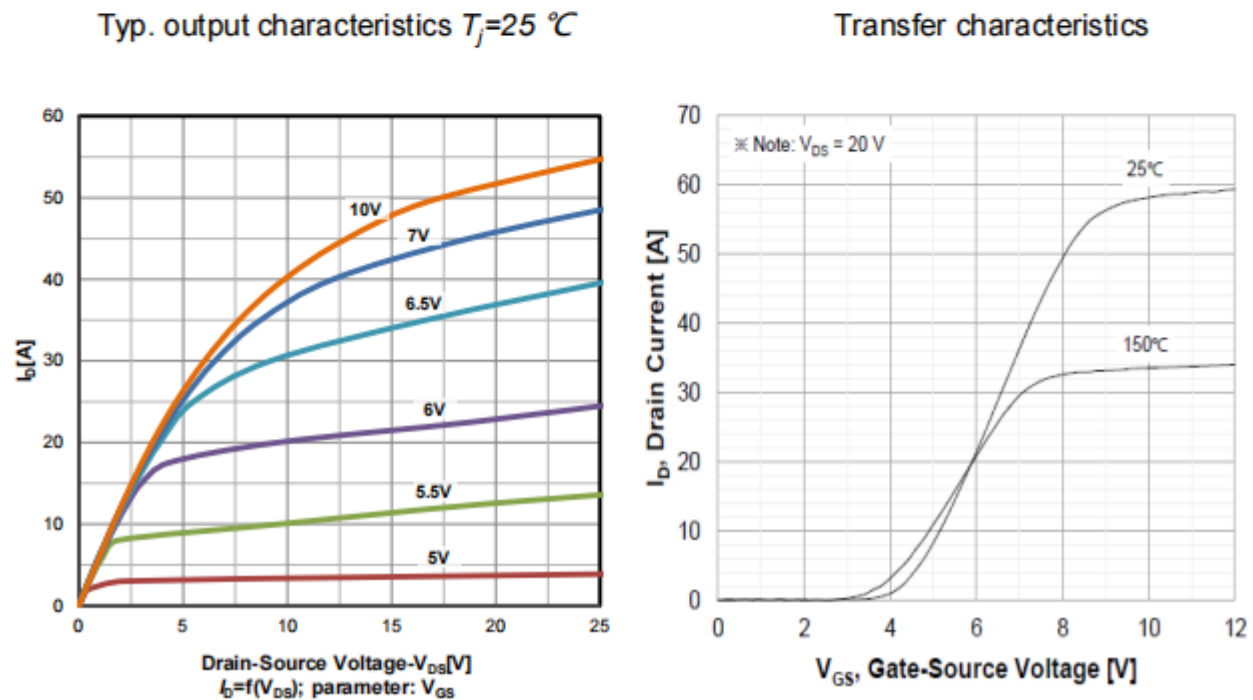
SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		800	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	1.08	-	V/°C
Gate-source threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
		V _{GS} = ± 30 V		-	-	± 1	μA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 800 V, V _{GS} = 0 V		-	-	1	μA
		V _{DS} = 640 V, V _{GS} = 0 V, T _J = 125 °C		-	-	10	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D =2.5A	-	0.550	-	Ω
Forward transconductance	g _{fs}	V _{DS} = 30 V, I _D = 5 A		-	8.7	-	S
Dynamic							
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz		-	2200	-	pF
Output capacitance	C _{oss}			-	51	-	
Reverse transfer capacitance	C _{rss}			-	12	-	
Effective output capacitance, energy related ^a	C _{o(er)}	V _{DS} = 0 V to 480 V, V _{GS} = 0 V		-	52	-	
Effective output capacitance, time related ^b	C _{o(tr)}			-	205	-	
Total gate charge	Q _g	V _{GS} = 10 V	I _D = 5 A, V _{DS} = 480 V	-	25	-	nC
Gate-source charge	Q _{gs}			-	8	-	
Gate-drain charge	Q _{gd}			-	10	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 480 V, I _D = 5 A, V _{GS} = 10 V, R _g = 9.1 Ω		-	12	24	ns
Rise time	t _r			-	14	23	
Turn-off delay time	t _{d(off)}			-	61	110	
Fall time	t _f			-	16	-	
Gate input resistance	R _g	f = 1 MHz, open drain		0.3	0.7	1.4	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	8	A
Pulsed diode forward current	I _{SM}			-	-	24	
Diode forward voltage	V _{SD}	T _J = 25 °C, I _S = 5 A, V _{GS} = 0 V		-	-	1.2	V
Reverse recovery time	t _{rr}	T _J = 25 °C, I _F = I _S = 5 A, dI/dt = 100 A/μs, V _R = 25 V		-	416	832	ns
Reverse recovery charge	Q _{rr}			-	6.4	12.8	μC
Reverse recovery current	I _{RRM}			-	27	-	A

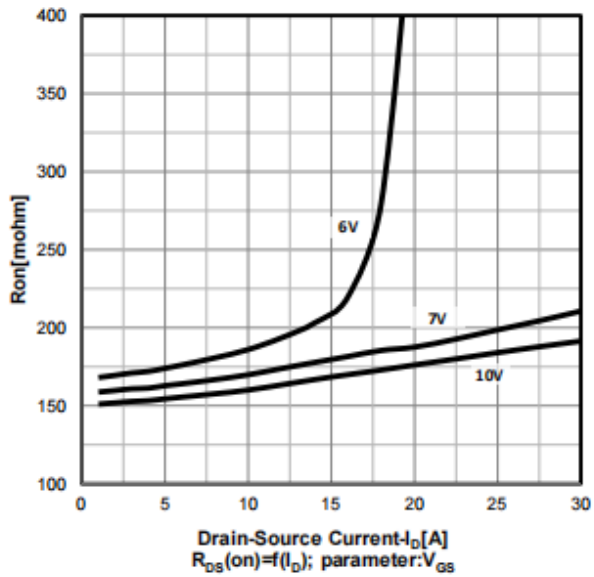
Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

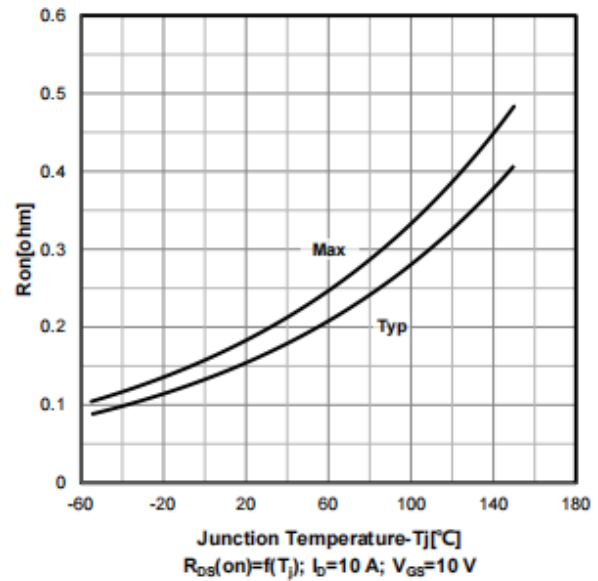
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Typ. drain-source on-state resistance



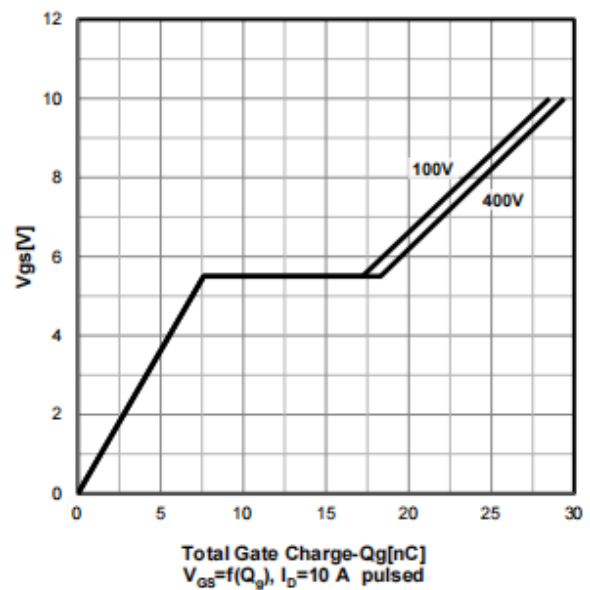
On-resistance vs temperature



Typ. capacitances



Typ. gate charge characteristics



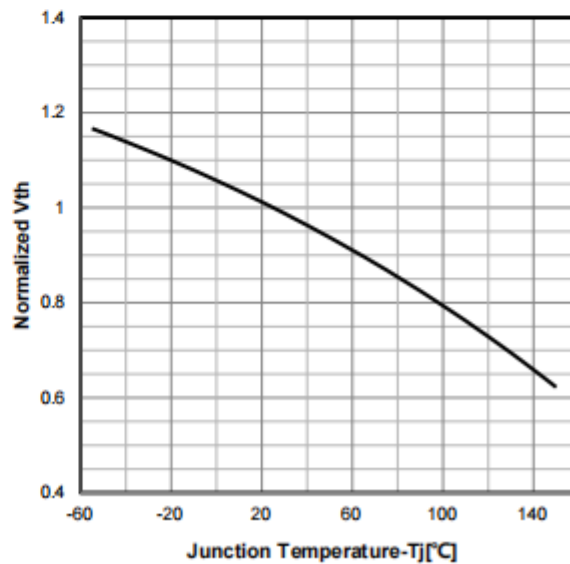
Drain current vs temperature



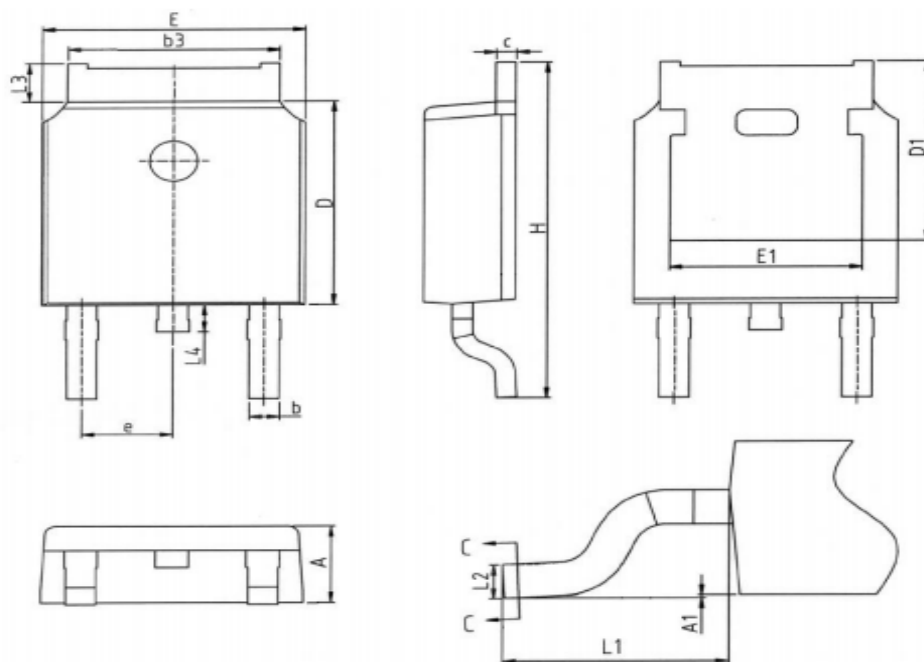
Forward characteristics of reverse diode



Drain-source breakdown voltage

Normalized $V_{GS(th)}$ characteristics

Package Outline : TO 252



COMMON DIMENSIONS

SYMBOL	UNIT(mm)		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	-	0.127
b	0.66	0.78	0.90
b3	5.16	5.31	5.46
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.75
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L1	2.90REF		
L2	0.51BSC		
L3	0.88	1.08	1.28
L4	0.50	0.80	1.00

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